NGTB30N135IHR1WG

IGBT with Monolithic Free Wheeling Diode

This Insulated Gate Bipolar Transistor (IGBT) features a robust and cost effective Field Stop (FS) Trench construction, provides superior performance in demanding switching applications, and offers low on−state voltage with minimal switching losses. The IGBT is well suited for resonant or soft switching applications.

Features

- Extremely Efficient Trench with Fieldstop Technology
- 1350 V Breakdown Voltage
- Optimized for Low Losses in IH Cooker Application
- Designed for High System Level Robustness
- These are Pb−Free Devices

Typical Applications

- Inductive Heating
- Consumer Appliances
- Soft Switching

ABSOLUTE MAXIMUM RATINGS

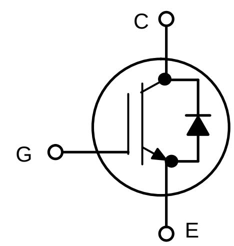
Rating	Symbol	Value	Unit
Collector−emitter voltage @ T_J = 25°C	V_{CES}	1350	V
Collector current @ T_C = 25°C @ T_C = 100°C	I_C	 60 30	A
Pulsed collector current, T_{pulse} limited by T_{Jmax} 10 μs pulse, V_{GE} = 15 V	I_{CM}	120	A
Diode forward current @ T_C = 25°C @ T_C = 100°C	I_F	 60 30	A
Diode pulsed current, T_{pulse} limited by T_{Jmax} 10 μs pulse, V_{GE} = 0 V	I_{FM}	120	A
Gate−emitter voltage Transient Gate−emitter Voltage (T_{pulse} = 5 μs, D < 0.10)	V_{GE}	±20 ±25	V
Power Dissipation @ T_C = 25°C @ T_C = 100°C	P_D	 394 197	W
Operating junction temperature range	T_J	−40 to +175	°C
Storage temperature range	T_{stg}	−55 to +175	°C
Lead temperature for soldering, 1/8" from case for 5 seconds	T_{SLD}	260	°C

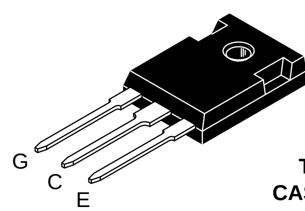
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

ON Semiconductor®

www.onsemi.com

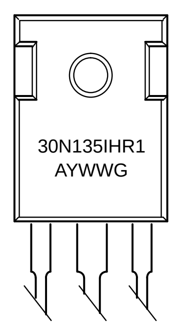
30 A, 1350 V
V_{CEsat} = 2.4 V
E_{off} = 0.63 mJ





TO−247
CASE 340AL

MARKING DIAGRAM



A = Assembly Location
Y = Year
WW = Work Week
G = Pb−Free Package

ORDERING INFORMATION

Device	Package	Shipping
NGTB30N135IHR1WG	TO−247 (Pb−Free)	30 Units / Rail

THERMAL CHARACTERISTICS

Rating	Symbol	Value	Unit
Thermal resistance junction−to−case	$R_{\theta JC}$	0.38	°C/W
Thermal resistance junction−to−ambient	$R_{\theta JA}$	40	°C/W

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
STATIC CHARACTERISTIC						
Collector−emitter breakdown voltage, gate−emitter short−circuited	V_{GE} = 0 V, I_C = 5 mA	$V_{(BR)CES}$	1350	−	−	V
Collector−emitter saturation voltage	V_{GE} = 15 V, I_C = 30 A V_{GE} = 15 V, I_C = 30 A, T_J = 175°C	V_{CEsat}	− −	2.4 2.6	3.0 −	V
Gate−emitter threshold voltage	V_{GE} = V_{CE}, I_C = 250 μA	$V_{GE(th)}$	4.5	5.5	6.5	V
Collector−emitter cut−off current, gate−emitter short−circuited	V_{GE} = 0 V, V_{CE} = 1350 V V_{GE} = 0 V, V_{CE} = 1350 V, T_J = 175°C	I_{CES}	− −	− −	0.5 5.0	mA
Gate leakage current, collector−emitter short−circuited	V_{GE} = 20 V, V_{CE} = 0 V	I_{GES}	−	−	100	nA
DYNAMIC CHARACTERISTIC						
Input capacitance	V_{CE} = 20 V, V_{GE} = 0 V, f = 1 MHz	C_{ies}	−	5530	−	pF
Output capacitance		C_{oes}	−	124	−	
Reverse transfer capacitance		C_{res}	−	100	−	
Gate charge total	V_{CE} = 600 V, I_C = 30 A, V_{GE} = 15 V	Q_g	−	220	−	nC
Gate to emitter charge		Q_{ge}	−	47	−	
Gate to collector charge		Q_{gc}	−	100	−	
SWITCHING CHARACTERISTIC, INDUCTIVE LOAD						
Turn−off delay time	T_J = 25°C V_{CC} = 600 V, I_C = 30 A R_g = 10 Ω V_{GE} = 0 V/ 15V	$t_{d(off)}$	−	200	−	ns
Fall time		t_f	−	124	−	
Turn−off switching loss		E_{off}	−	0.63	−	mJ
Turn−off delay time	T_J = 150°C V_{CC} = 600 V, I_C = 30 A R_g = 10 Ω V_{GE} = 0 V/ 15V	$t_{d(off)}$	−	222	−	ns
Fall time		t_f	−	221	−	
Turn−off switching loss		E_{off}	−	1.50	−	mJ
DIODE CHARACTERISTIC						
Forward voltage	V_{GE} = 0 V, I_F = 30 A V_{GE} = 0 V, I_F = 30 A, T_J = 175°C	V_F	− −	1.7 2.1	2.2 −	V

TYPICAL CHARACTERISTICS

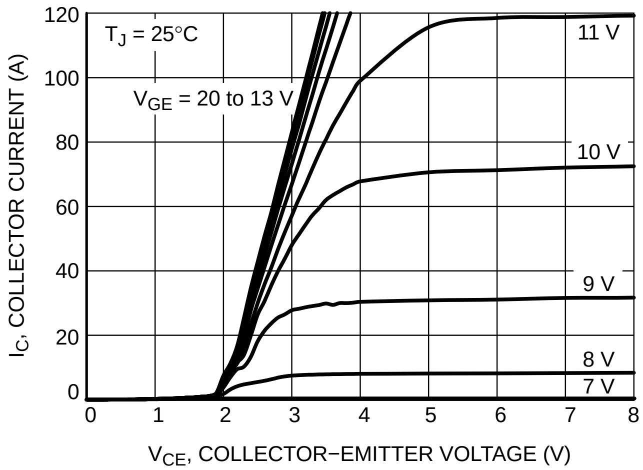


Figure 1. Output Characteristics

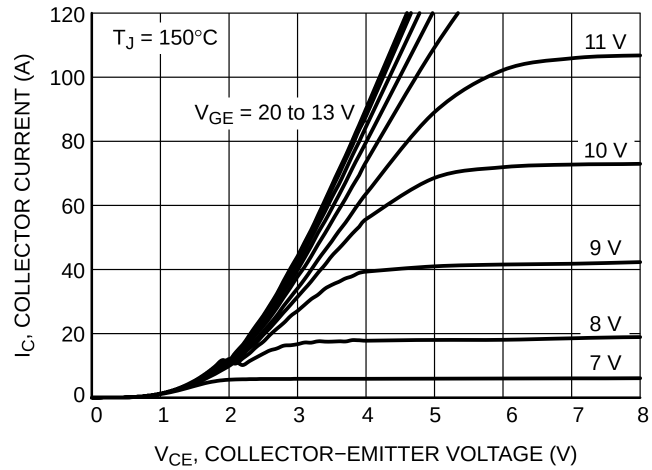


Figure 2. Output Characteristics

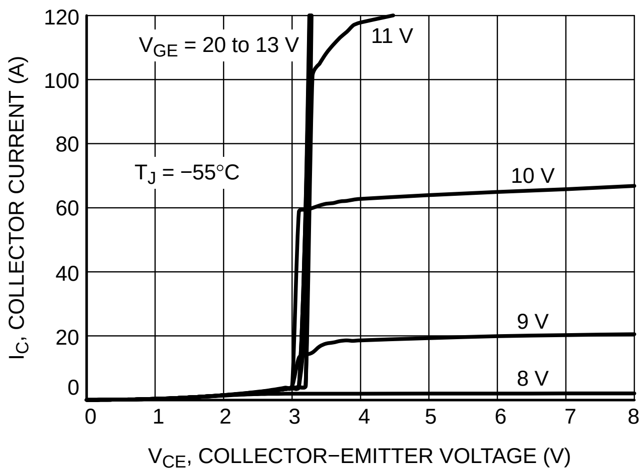


Figure 3. Output Characteristics

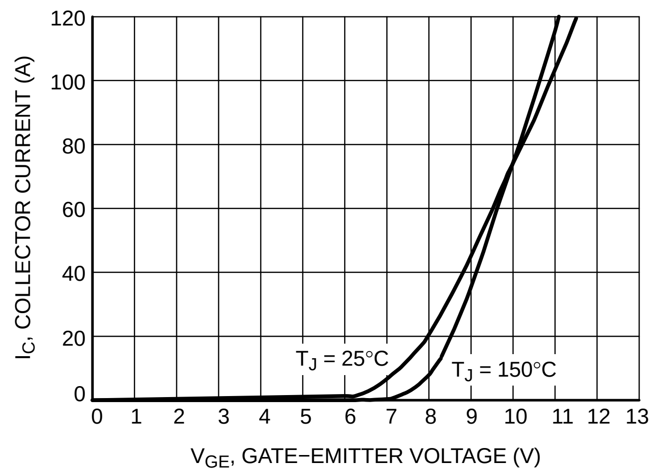


Figure 4. Typical Transfer Characteristics

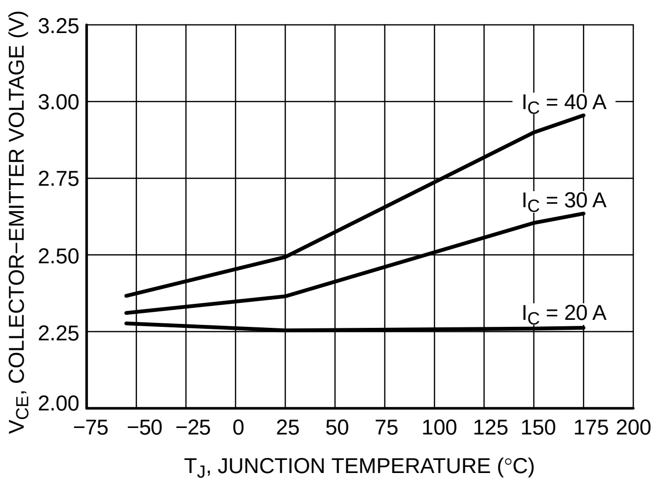


Figure 5. $V_{CE(sat)}$ vs. T_J

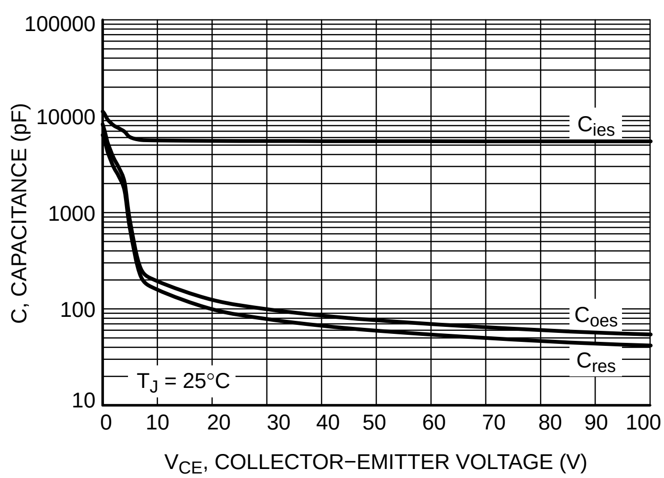


Figure 6. Typical Capacitance

TYPICAL CHARACTERISTICS

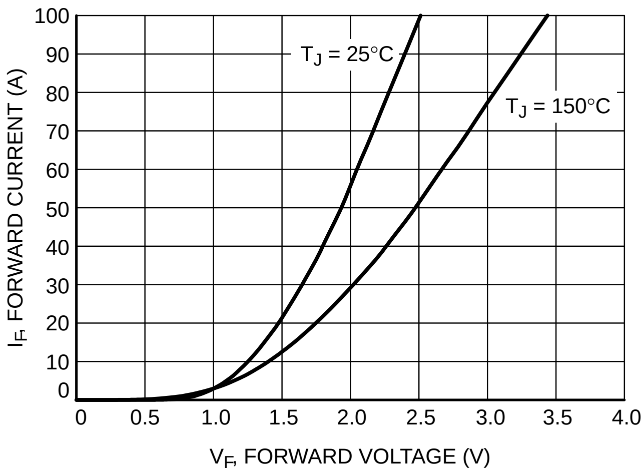


Figure 7. Diode Forward Characteristics

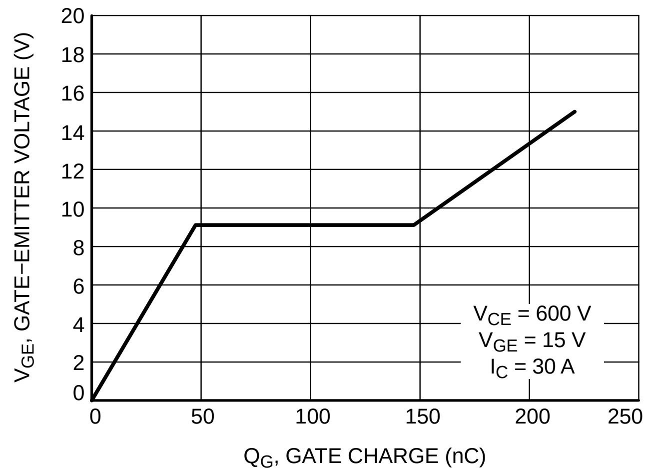


Figure 8. Typical Gate Charge

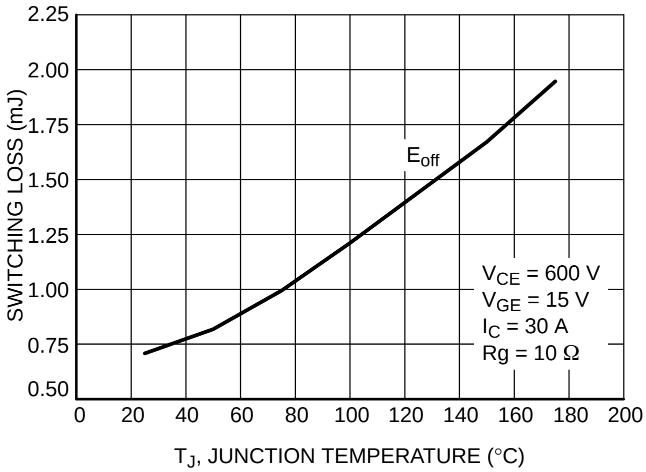


Figure 9. Switching Loss vs. Temperature

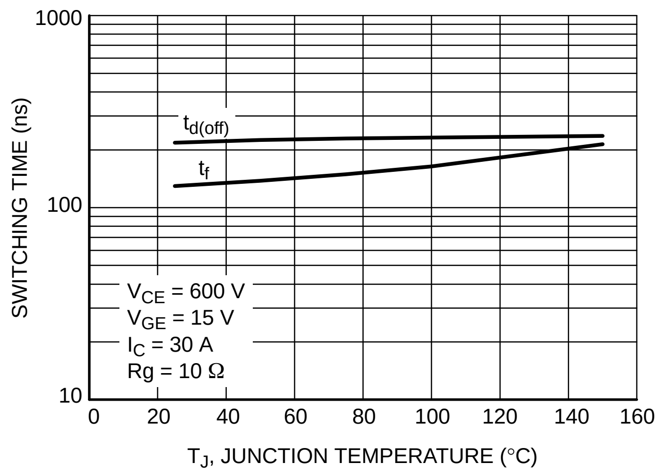


Figure 10. Switching Time vs. Temperature

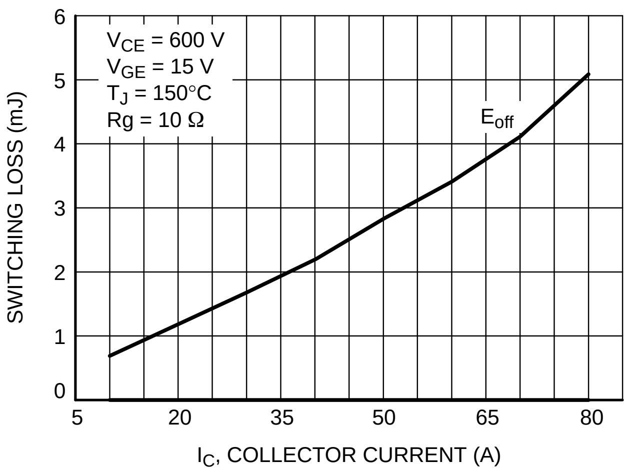


Figure 11. Switching Loss vs. I_C

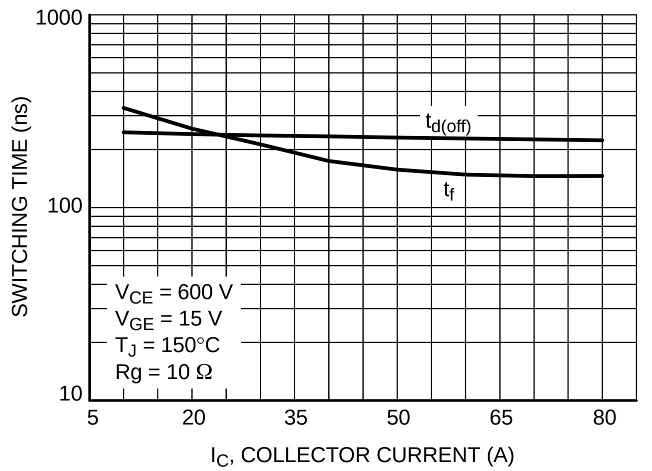


Figure 12. Switching Time vs. I_C

TYPICAL CHARACTERISTICS

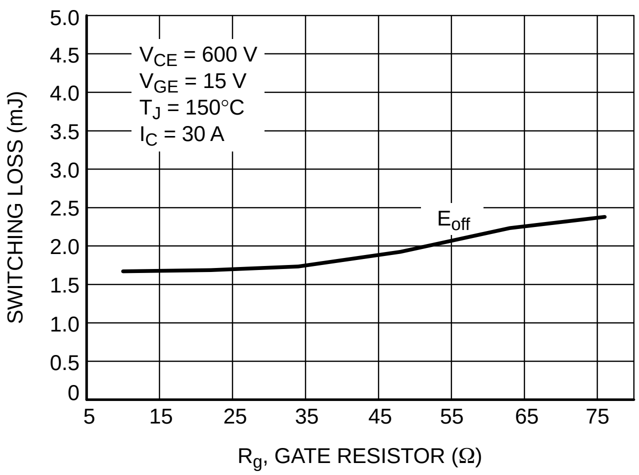


Figure 13. Switching Loss vs. R_g

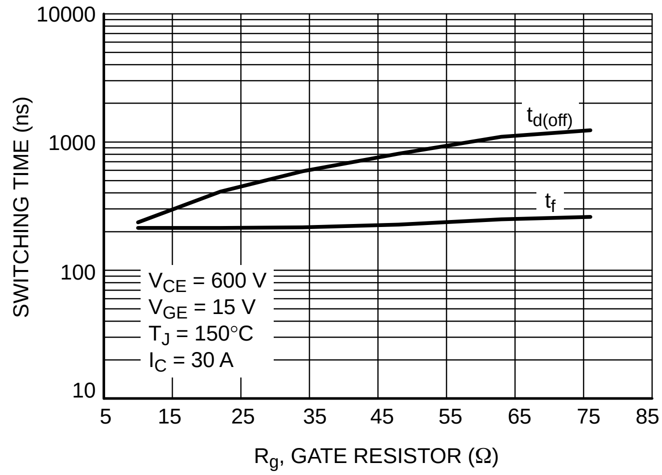


Figure 14. Switching Time vs. R_g

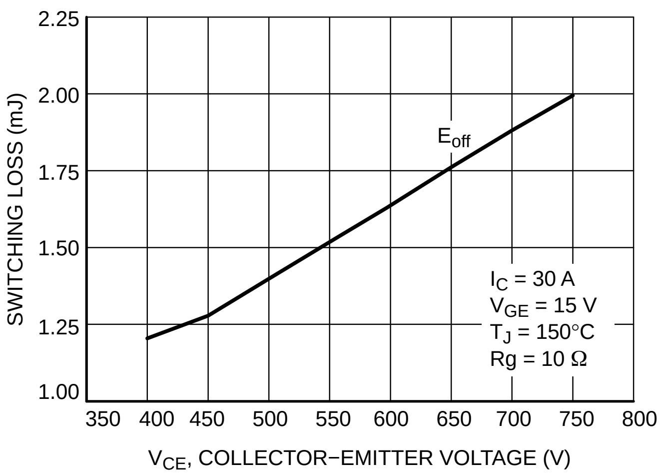


Figure 15. Switching Loss vs. V_{CE}

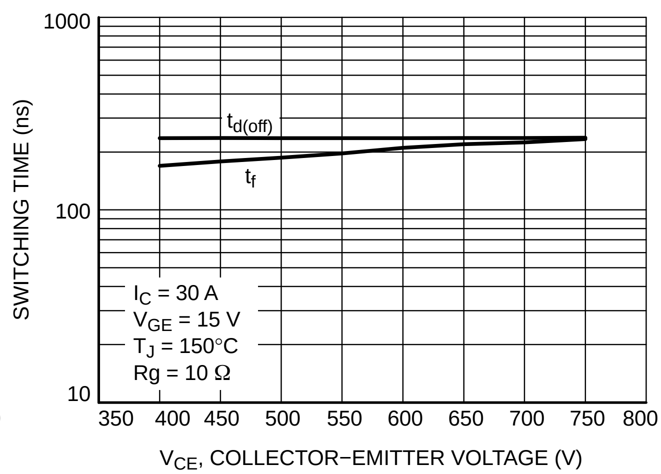


Figure 16. Switching Time vs. V_{CE}

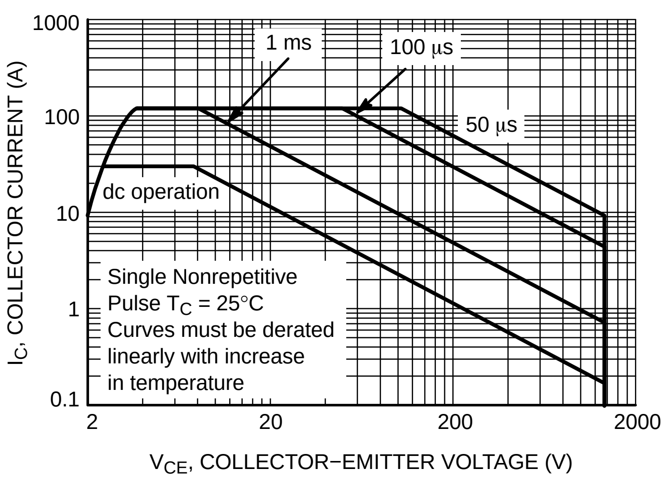


Figure 17. Safe Operating Area

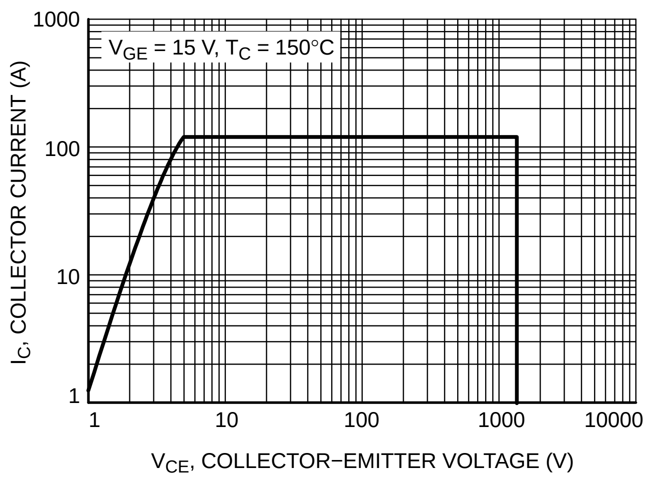


Figure 18. Reverse Bias Safe Operating Area

TYPICAL CHARACTERISTICS

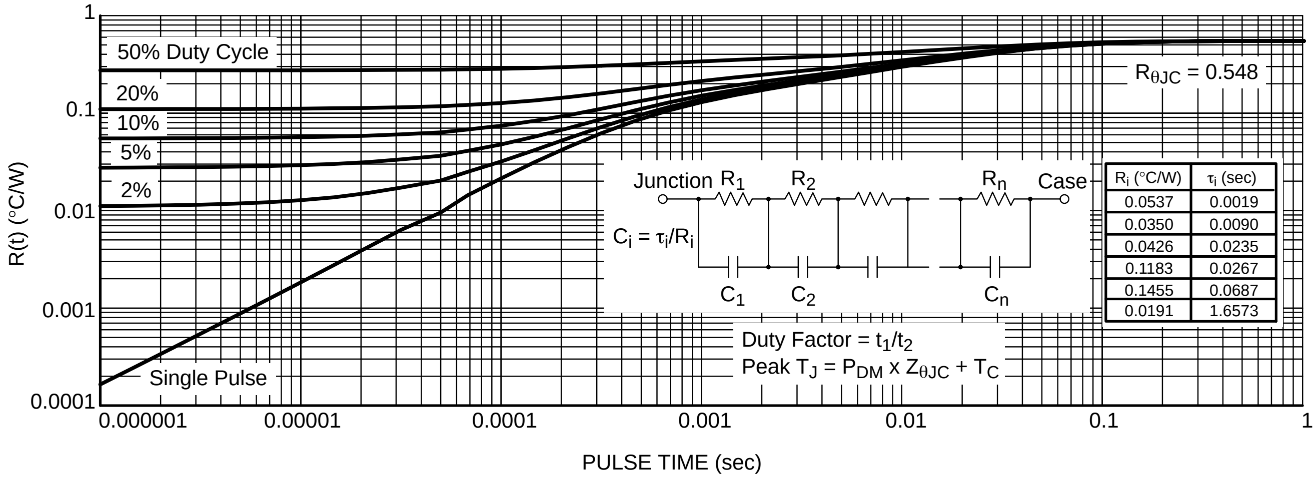


Figure 19. IGBT Transient Thermal Impedance

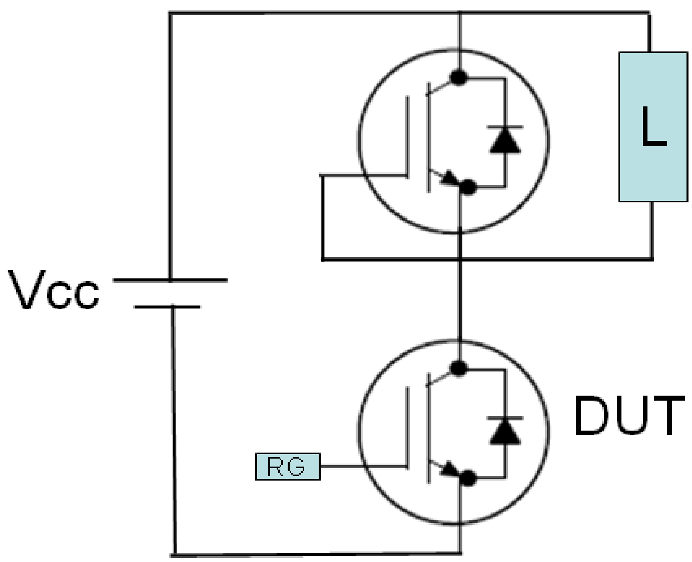


Figure 20. Test Circuit for Switching Characteristics

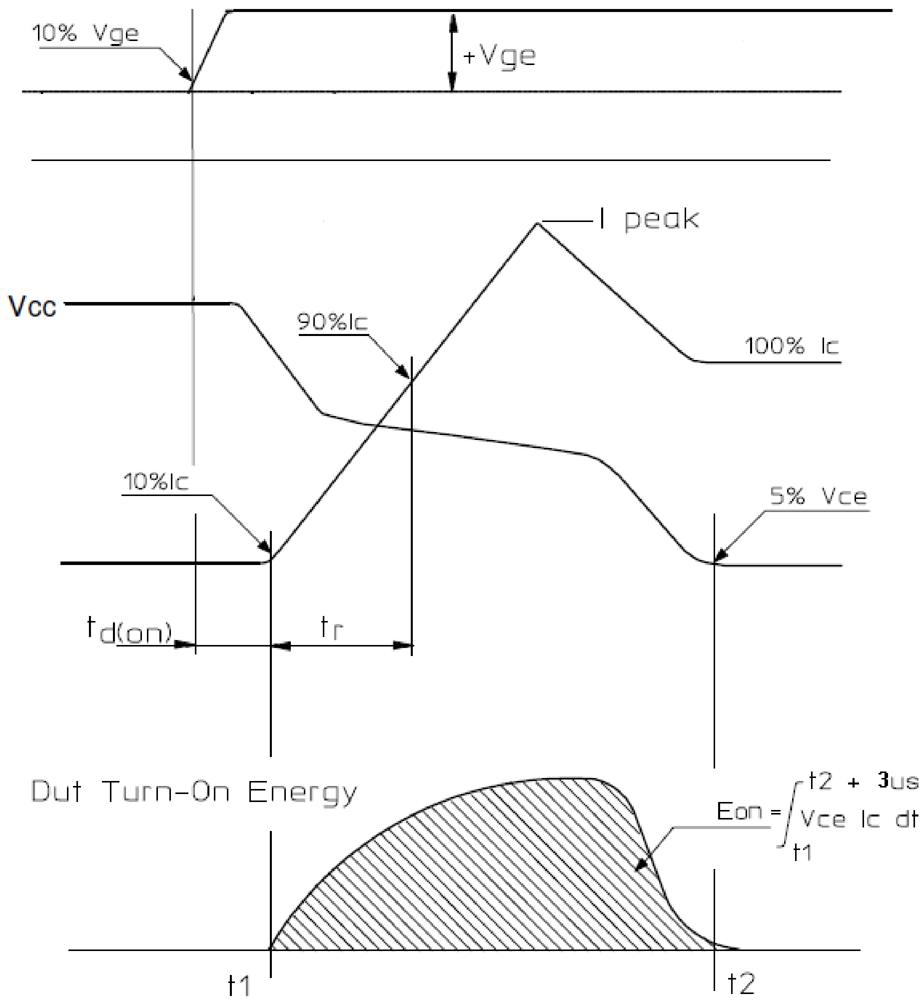


Figure 21. Definition of Turn On Waveform

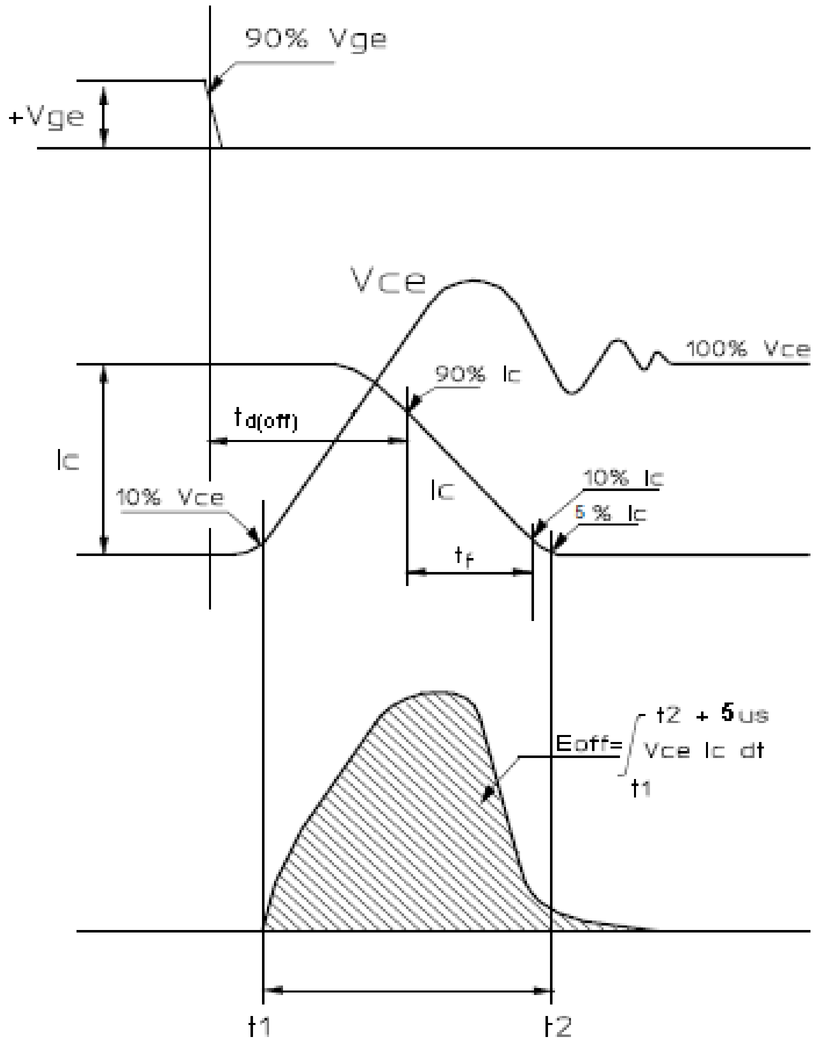
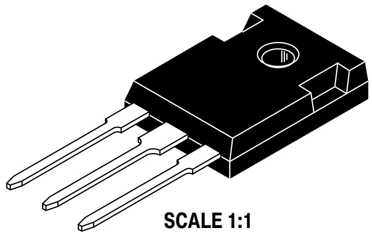
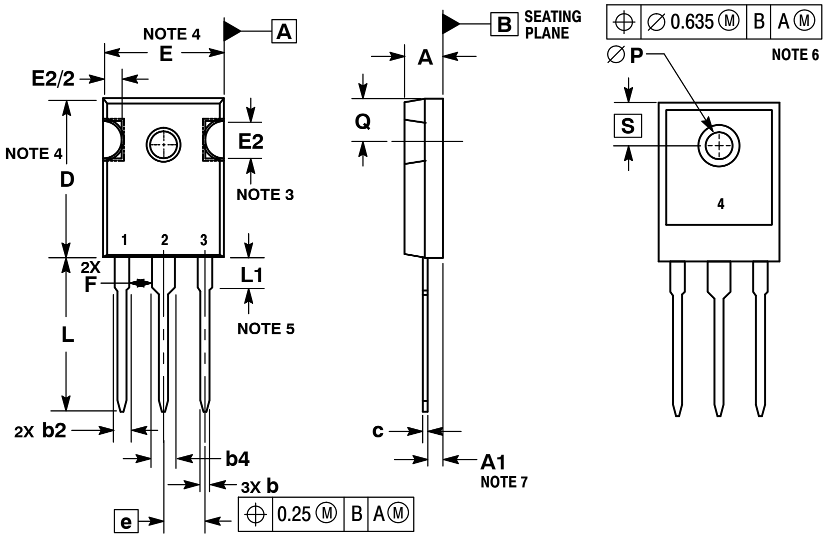


Figure 22. Definition of Turn Off Waveform



TO−247
CASE 340AL
ISSUE D

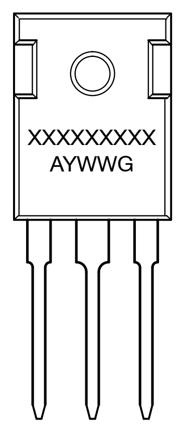
DATE 17 MAR 2017



NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. SLOT REQUIRED, NOTCH MAY BE ROUNDED.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.13 PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREME OF THE PLASTIC BODY.
5. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.
6. ∅P SHALL HAVE A MAXIMUM DRAFT ANGLE OF 1.5° TO THE TOP OF THE PART WITH A MAXIMUM DIAMETER OF 3.91.
7. DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED BY L1.

	MILLIMETERS	
DIM	MIN	MAX
A	4.70	5.30
A1	2.20	2.60
b	1.07	1.33
b2	1.65	2.35
b4	2.60	3.40
c	0.45	0.68
D	20.80	21.34
E	15.50	16.25
E2	4.32	5.49
e	5.45 BSC	
F	2.655	---
L	19.80	20.80
L1	3.81	4.32
P	3.55	3.65
Q	5.40	6.20
S	6.15 BSC	

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
G = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking.
Pb−Free indicator, “G” or microdot “ ▪”, may or may not be present.

DOCUMENT NUMBER:	98AON16119F	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped “CONTROLLED COPY” in red.
DESCRIPTION:	TO−247	PAGE 1 OF 1

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:
Technical Library: www.onsemi.com/design/resources/technical−documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support
For additional information, please contact your local Sales Representative at
www.onsemi.com/support/sales

◊